RESPONSE TO RESTRICTION REQUIREMENT AND PRELIMINARY AMENDMENT

Serial Number: 09/653,640 Filing Date: August 31, 2000

Title: CONTACT STRUCTURE

PECEIVED

Page 2 Dkt: 303.703US1

APR 25 2002

or more layers including platinum-iridium; and

an structure encircling the one or more layers.

98. (New) The integrated circuit of claim 97, wherein one of the one or more layers comprises a layer of tungsten nitride having a thickness of between about 900 angstroms and 1100 angstroms.

99. (New) The integrated circuit device of claim 97, wherein the second device is a bipolar transistor.

100.

(New) An integrated circuit comprising:

a first device.

a second device;

one or more layers coupling the first device to the second device, at least one of the one or more layers including platinum-rhodium; and

a structure encircling at least two of the one or more layers.

w Colling

- 101. (New) The integrated circuit of claim 100, wherein the one or more layers includes a polysilicon layer.
- 102. (New) The integrated circuit of claim 100, wherein the first device is formed in a substrate, the substrate selected from a group consisting of silicon, germanium, gallium-arsenide, and silicon-on-sapphire.

Claims 94-102 have been added; as a result, claims 19-36 and 94-102 are now pending in this application. The added claims are supported in the specification as originally filed. No new matter has been added.